

# Adam T Neal

## List of Publications by Year in descending order

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37  
papers

8,863  
citations

304368

22  
h-index

414034

32  
g-index

37  
all docs

37  
docs citations

37  
times ranked

11351  
citing authors

#	ARTICLE	IF	CITATIONS
1	Phosphorene: An Unexplored 2D Semiconductor with a High Hole Mobility. ACS Nano, 2014, 8, 4033-4041.	7.3	5,474
2	Channel Length Scaling of MoS <sub>2</sub> MOSFETs. ACS Nano, 2012, 6, 8563-8569.	7.3	688
3	Demonstration of high mobility and quantum transport in modulation-doped $\hat{\Gamma}^2$ -(Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> /Ga <sub>2</sub> O <sub>3</sub> heterostructures. Applied Physics Letters, 2018, 112, .	1.5	264
4	Molecular Doping of Multilayer $\{m \text{ MoS}_2\}$ Field-Effect Transistors: Reduction in Sheet and Contact Resistances. IEEE Electron Device Letters, 2013, 34, 1328-1330.	2.2	231
5	Switching Mechanism in Single-Layer Molybdenum Disulfide Transistors: An Insight into Current Flow across Schottky Barriers. ACS Nano, 2014, 8, 1031-1038.	7.3	224
6	Donors and deep acceptors in $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> . Applied Physics Letters, 2018, 113, .	1.5	203
7	Statistical Study of Deep Submicron Dual-Gated Field-Effect Transistors on Monolayer Chemical Vapor Deposition Molybdenum Disulfide Films. Nano Letters, 2013, 13, 2640-2646.	4.5	197
8	$\hat{\Gamma}^2$ -Gallium oxide power electronics. APL Materials, 2022, 10, .	2.2	184
9	Ge-Doped $\{\eta\}$ -Ga <sub>2</sub> O <sub>3</sub> MOSFETs. IEEE Electron Device Letters, 2017, 38, 775-778.	2.2	165
10	The Effect of Dielectric Capping on Few-Layer Phosphorene Transistors: Tuning the Schottky Barrier Heights. IEEE Electron Device Letters, 2014, 35, 795-797.	2.2	154
11	Heteroepitaxy of N-type $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> thin films on sapphire substrate by low pressure chemical vapor deposition. Applied Physics Letters, 2016, 109, .	1.5	122
12	Intrinsic doping and gate hysteresis in graphene field effect devices fabricated on SiO <sub>2</sub> substrates. Journal of Physics Condensed Matter, 2010, 22, 334214.	0.7	116
13	Magneto-transport in MoS <sub>2</sub> : Phase Coherence, Spin-Orbit Scattering, and the Hall Factor. ACS Nano, 2013, 7, 7077-7082.	7.3	88
14	Lateral $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> field effect transistors. Semiconductor Science and Technology, 2020, 35, 013002.	1.0	85
15	Incomplete Ionization of a 110 meV Unintentional Donor in $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> and its Effect on Power Devices. Scientific Reports, 2017, 7, 13218.	1.6	84
16	Towards High-Mobility Heteroepitaxial $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> on Sapphire $\hat{\Gamma}^2$ Dependence on The Substrate Off-Axis Angle. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700467.	0.8	84
17	MOCVD growth of high purity Ga <sub>2</sub> O <sub>3</sub> epitaxial films using trimethylgallium precursor. Applied Physics Letters, 2020, 117, .	1.5	77
18	Effects of (NH <sub>4</sub> ) <sub>2</sub> S passivation on the off-state performance of 3-dimensional InGaAs metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2011, 99, .	1.5	71

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19	P-type conduction in two-dimensional MoS <sub>2</sub> via oxygen incorporation. Applied Physics Letters, 2017, 110, .	1.5	64
20	Size-Dependent-Transport Study of $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ Gate-All-Around Nanowire MOSFETs: Impact of Quantum Confinement and Volume Inversion. IEEE Electron Device Letters, 2012, 33, 967-969.	2.2	49
21	Two-Dimensional TaSe <sub>2</sub> Metallic Crystals: Spin-Orbit Scattering Length and Breakdown Current Density. ACS Nano, 2014, 8, 9137-9142.	7.3	49
22	Metal contacts to MoS <sub>2</sub> : A two-dimensional semiconductor. , 2012, , .		41
23	Pulsed Power Performance of $\text{InGaAs}$ MOSFETs at L-Band. IEEE Electron Device Letters, 2020, 41, 989-992.	2.2	32
24	Reduction of unintentional Si doping in $\text{InGaAs}$ grown via plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 043403.	0.9	20
25	(Invited) Fundamentals in MoS <sub>2</sub> Transistors: Dielectric, Scaling and Metal Contacts. ECS Transactions, 2013, 58, 203-208.	0.3	19
26	Weak localization in few-layer black phosphorus. 2D Materials, 2016, 3, 024003.	2.0	17
27	$\text{InGaAs}$ defect study by steady-state capacitance spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 091101.	0.8	17
28	Si doping in MOCVD grown (010) $\text{In}_{1-x}\text{Ga}_x\text{As}$ thin films. Journal of Applied Physics, 2022, 131, .	1.1	15
29	Transport studies in 2D transition metal dichalcogenides and black phosphorus. Journal of Physics Condensed Matter, 2016, 28, 263002.	0.7	12
30	(Invited) Atomic-Layer-Deposited High-k Dielectric Integration on Epitaxial Graphene. ECS Transactions, 2010, 33, 459-466.	0.3	5
31	Ambipolar phosphorene field-effect transistors with dielectric capping. , 2014, , .		4
32	(Invited) ALD High-k as a Common Gate Stack Solution for Nanoelectronics. ECS Transactions, 2010, 28, 51-68.	0.3	3
33	Study of defects in $\text{InGaAs}$ by isothermal capacitance transient spectroscopy. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2019, 37, 041204.	0.6	3
34	Electronic Transport Properties in Top-Gated Epitaxial Graphene on Silicon Carbide with ALD Al <sub>2</sub> O <sub>3</sub> High-K Dielectric. , 2010, , .		1
35	Zeeman spin-splitting in the (010) $\text{InGaAs}$ two-dimensional electron gas. Applied Physics Letters, 2019, 115, .	1.5	1
36	Pronounced quantum hall-effect on epitaxial graphene up to 70K. , 2009, , .		0

#	ARTICLE	IF	CITATIONS
37	Electrical Properties 1. Springer Series in Materials Science, 2020, , 389-405.	0.4	0